

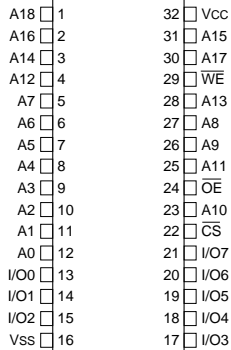


512Kx8 MONOLITHIC SRAM, SMD 5962-95613

EVOLUTIONARY PINOUT

32 DIP
32 CSOJ (DE)

TOP VIEW



PIN DESCRIPTION

A0-18	Address Inputs
I/O0-7	Data Input/Output
\overline{CS}	Chip Select
\overline{OE}	Output Enable
\overline{WE}	Write Enable
Vcc	+5.0V Power
GND	Ground

FEATURES

- Access Times 70, 85, 100, 120ns
- MIL-STD-883 Compliant Devices Available
- Evolutionary, Corner Power/Ground Pinout JEDEC Approved
 - 32 pin Ceramic DIP (Package 300)
 - 32 lead Ceramic SOJ (Package 101)
- Commercial, Industrial and Military Temperature Ranges
- 5 Volt Power Supply
- Low Power CMOS
- Low Power Data Retention
- TTL Compatible Inputs and Outputs



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-55	+125	°C
Storage Temperature	T _{STG}	-65	+150	°C
Signal Voltage Relative to GND	V _G	-0.5	V _{CC} +0.5	V
Junction Temperature	T _J		150	°C
Supply Voltage	V _{CC}	-0.5	7.0	V

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	4.5	5.5	V
Input High Voltage	V _{IH}	2.2	V _{CC} + 0.3	V
Input Low Voltage	V _{IL}	-0.3	+0.8	V
Operating Temp. (Mil.)	T _A	-55	+125	°C

TRUTH TABLE

\overline{CS}	\overline{OE}	\overline{WE}	Mode	Data I/O	Power
H	X	X	Standby	High Z	Standby
L	L	H	Read	Data Out	Active
L	X	L	Write	Data In	Active
L	H	H	Out Disable	High Z	Active

CAPACITANCE

(T_A = +25°C)

Parameter	Symbol	Condition	Max	Unit
Input capacitance	C _{IN}	V _{IN} = 0V, f = 1.0MHz	12	pF
Output capacitance	C _{OUT}	V _{OUT} = 0V, f = 1.0MHz	12	pF

This parameter is guaranteed by design but not tested.

DC CHARACTERISTICS

(V_{CC} = 5.0V, GND = 0V, T_A = -55°C to +125°C)

Parameter	Symbol	Conditions	Units		
			Min	Max	
Input Leakage Current	I _{LI}	V _{CC} = 5.5, V _{IN} = GND to V _{CC}		10	μA
Output Leakage Current	I _{LO}	\overline{CS} = V _{IH} , \overline{OE} = V _{IH} , V _{OUT} = GND to V _{CC}		10	μA
Operating Supply Current	I _{CC}	\overline{CS} = V _{IL} , \overline{OE} = V _{IH} , f = 5MHz, V _{CC} = 5.5		50	mA
Standby Current	I _{SB}	\overline{CS} = V _{IH} , \overline{OE} = V _{IH} , f = 5MHz, V _{CC} = 5.5		1	mA
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA, V _{CC} = 4.5		0.4	V
Output High Voltage	V _{OH}	I _{OH} = -1.0mA, V _{CC} = 4.5	2.4		V

NOTE: DC test conditions: V_{IH} = V_{CC} - 0.3V, V_{IL} = 0.3V

DATA RETENTION CHARACTERISTICS

(T_A = -55°C to +125°C)

Parameter	Symbol	Conditions	Military			Units
			Min	Typ	Max	
Data Retention Supply Voltage	V _{DR}	\overline{CS} ≥ V _{CC} - 0.2V	2.0		5.5	V
Data Retention Current	I _{CCDR1}	V _{CC} = 3V		100	400	μA

DATA RETENTION CHARACTERISTICS FOR LOW POWER “L” VERSION

Parameter	Symbol	Conditions	Units		
			Min	Max	
Data Retention Supply Voltage	V _{DR}	\overline{CS} ≥ V _{CC} - 0.2V	2.0	5.5	V
Low Power Data Retention (L)	I _{CCDR1}	V _{CC} = 2V		185	μA



AC CHARACTERISTICS

(V_{CC} = 5.0V, GND = 0V, T_A = -55°C to +125°C)

Parameter	Symbol	-70		-85		-100		-120		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	t _{RC}	70		85		100		120		ns
Address Access Time	t _{AA}		70		85		100		120	ns
Output Hold from Address Change	t _{OH}	5		5		5		5		ns
Chip Select Access Time	t _{ACS}		70		85		100		120	ns
Output Enable to Output Valid	t _{OE}		35		40		50		60	ns
Chip Select to Output in Low Z	t _{CLZ'}	10		10		10		10		ns
Output Enable to Output in Low Z	t _{OLZ'}	5		5		5		5		ns
Chip Disable to Output in High Z	t _{CHZ'}		25		25		35		35	ns
Output Disable to Output in High Z	t _{OHZ'}		25		25		35		35	ns

1. This parameter is guaranteed by design but not tested.

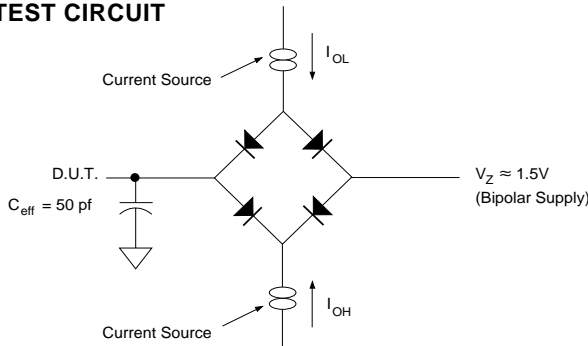
AC CHARACTERISTICS

(V_{CC} = 5.0V, GND = 0V, T_A = -55°C to +125°C)

Parameter	Symbol	-70		-85		-100		-120		Units
		Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{WC}	70		85		100		120		ns
Chip Select to End of Write	t _{CW}	60		75		80		100		ns
Address Valid to End of Write	t _{AW}	60		75		80		100		ns
Data Valid to End of Write	t _{DW}	30		30		40		40		ns
Write Pulse Width	t _{WP}	50		50		60		60		ns
Address Setup Time	t _{AS}	0		0		0		0		ns
Address Hold Time	t _{AH}	5		5		5		5		ns
Output Active from End of Write	t _{OW'}	5		5		5		5		ns
Write Enable to Output in High Z	t _{WHZ'}		25		25		35		35	ns
Data Hold from Write Time	t _{DH}	0		0		0		0		ns

1. This parameter is guaranteed by design but not tested.

AC TEST CIRCUIT



AC TEST CONDITIONS

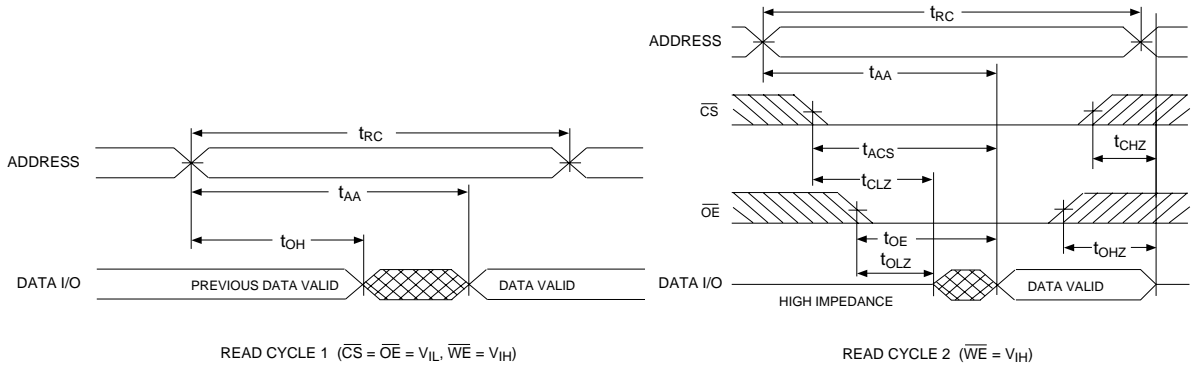
Parameter	Typ	Unit
Input Pulse Levels	V _{IL} = 0, V _{IH} = 3.0	V
Input Rise and Fall	5	ns
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

NOTES:

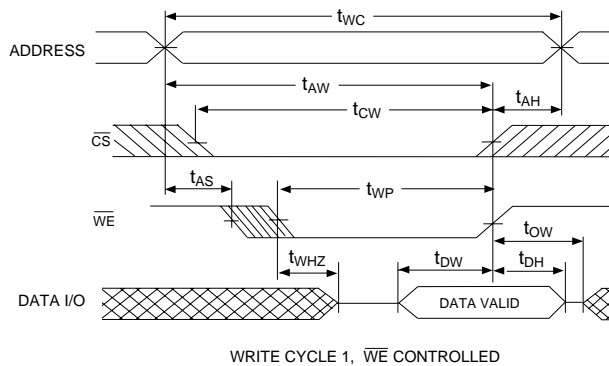
V_Z is programmable from -2V to +7V.
 I_{OL} & I_{OH} programmable from 0 to 16mA.
 Tester Impedance Z₀ = 75 Ω.
 V_Z is typically the midpoint of V_{OH} and V_{OL}.
 I_{OL} & I_{OH} are adjusted to simulate a typical resistive load circuit.
 ATE tester includes jig capacitance.



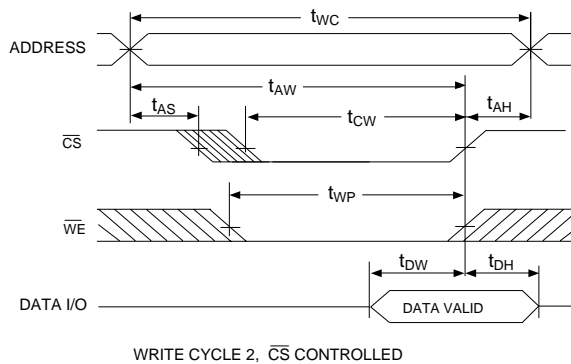
TIMING WAVEFORM - READ CYCLE



WRITE CYCLE - \overline{WE} CONTROLLED

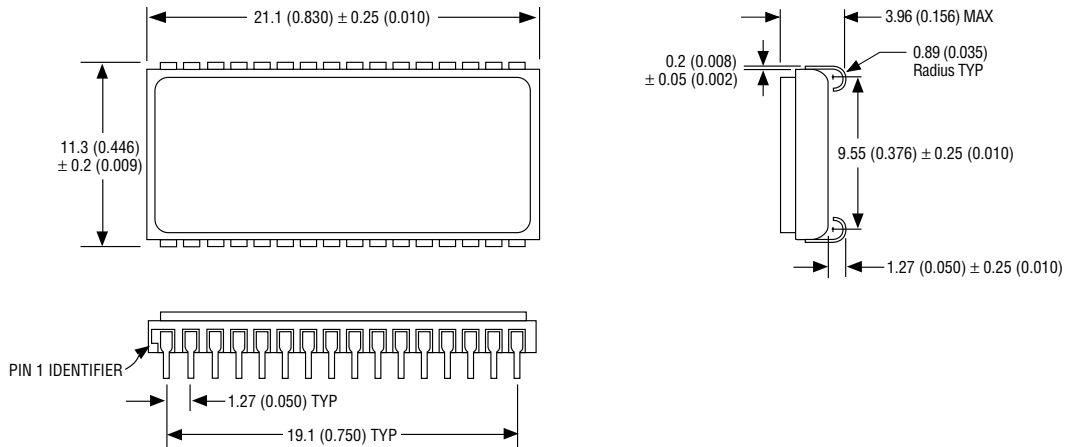


WRITE CYCLE - \overline{CS} CONTROLLED



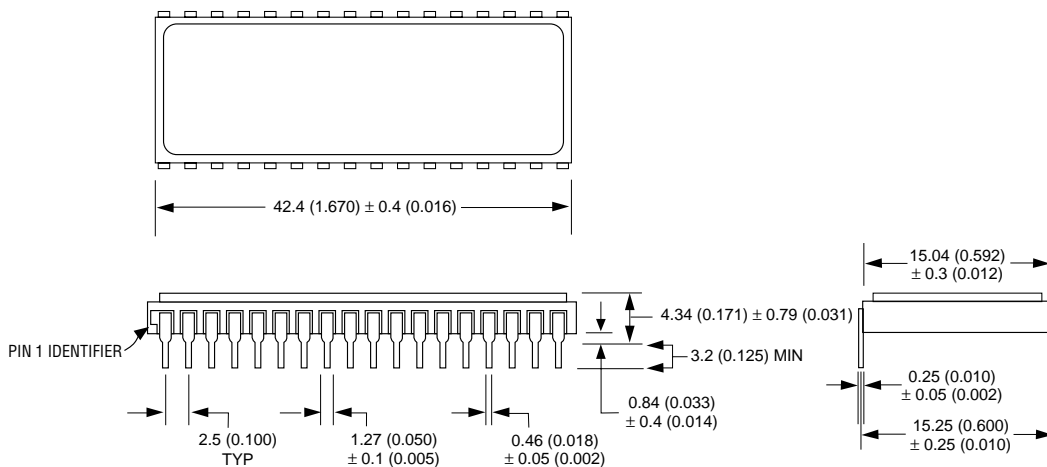


PACKAGE 101: 32 LEAD, CERAMIC SOJ

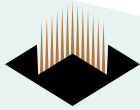


ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

PACKAGE 300: 32 PIN, CERAMIC DIP, SINGLE CAVITY SIDE BRAZED

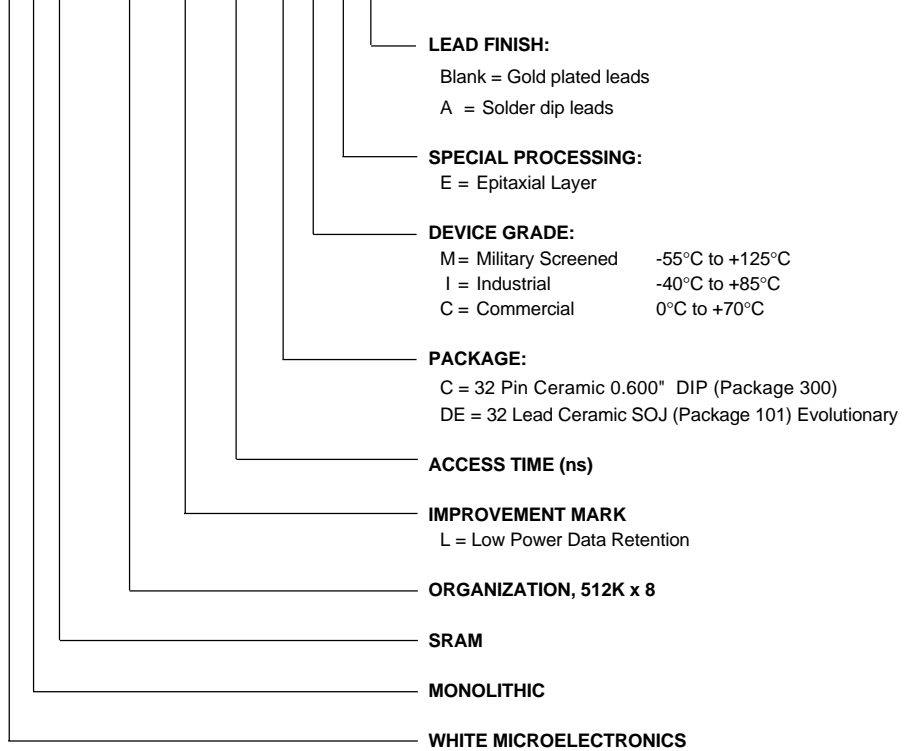


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ORDERING INFORMATION

W M S 512K 8 L - XXX X X X X



DEVICE TYPE	SPEED	PACKAGE	SMD NO.
512K x 8 SRAM Monolithic	120ns	32 pin DIP (C)	5962-95613 01HYX
512K x 8 SRAM Monolithic	100ns	32 pin DIP (C)	5962-95613 02HYX
512K x 8 SRAM Monolithic	85ns	32 pin DIP (C)	5962-95613 03HYX
512K x 8 SRAM Monolithic	70ns	32 pin DIP (C)	5962-95613 04HYX
512K x 8 SRAM Monolithic	120ns	32 lead SOJ Evol (DE)	5962-95613 01HTX
512K x 8 SRAM Monolithic	100ns	32 lead SOJ Evol (DE)	5962-95613 02HTX
512K x 8 SRAM Monolithic	85ns	32 lead SOJ Evol (DE)	5962-95613 03HTX
512K x 8 SRAM Monolithic	70ns	32 lead SOJ Evol (DE)	5962-95613 04HTX